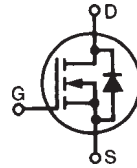


TrenchMV™ Power MOSFET

IOTP60N10TM

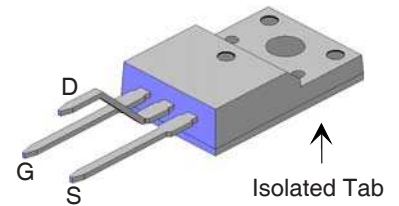
N-Channel Enhancement Mode
Avalanche Rated



$$\begin{aligned} V_{DSS} &= 100V \\ I_{D25} &= 33A \\ R_{DS(on)} &\leq 19m\Omega \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	100	V
V_{DGR}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}, R_{GS} = 1M\Omega$	100	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	33	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	180	A
I_A	$T_C = 25^\circ\text{C}$	10	A
E_{AS}	$T_C = 25^\circ\text{C}$	500	mJ
P_D	$T_C = 25^\circ\text{C}$	60	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	1.6mm (0.062in.) from case for 10s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in
Weight		2.5	g

OVERMOLDED TO-220 W/ FORMED
LEAD (IOTP...M)



G = Gate D = Drain
S = Source

Features

- Plastic overmolded tab for electrical isolation
- Low $R_{DS(ON)}$
 - for minimum on-state conduction losses
- Fast switching

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor drives
- Uninterruptible power supplies
- High speed power switching applications

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 50\mu A$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 150^\circ\text{C}$			1 μA 100 μA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 25A$, Notes 1, 2			19 m Ω

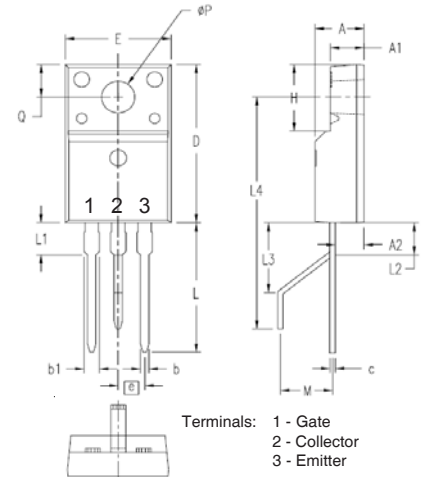
Symbol	Test Conditions	Characteristic Values		
(T _J = 25°C unless otherwise specified)		Min.	Typ.	Max.
g _{fs}	V _{DS} = 10V, I _D = 0.5 • I _{D25} , Note 1	25	42	S
C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		2650	pF
C _{oss}			335	pF
C _{rss}			60	pF
t _{d(on)}	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 10A R _G = 15Ω (External)		27	ns
t _r			40	ns
t _{d(off)}			43	ns
t _f			37	ns
Q _{g(on)}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 10A		49	nC
Q _{gs}			15	nC
Q _{gd}			11	nC
R _{thJC}				2.5 °C/W

Source-Drain Diode

Symbol	Test Conditions T _J = 25°C unless otherwise specified)	Characteristic Values			
		Min.	Typ.	Max.	
I _S	V _{GS} = 0V			60	A
I _{SM}	Repetitive, pulse width limited by T _{JM}			240	A
V _{SD}	I _F = 25A, V _{GS} = 0V, Note 1			1.2	V
t _{rr}	I _F = 30A, V _{GS} = 0V -di/dt = 100A/μs V _R = 50V		59		ns
I _{RM}			3.8		A
Q _{RM}			112		nC

- Notes
1. Pulse test, $t \leq 300 \mu\text{s}$; duty cycle, $d \leq 2\%$.
 2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

OVERMOLDED TO-220 W/ FORMED LEAD (IXTP...M)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.016	.024	0.40	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.500	.523	12.70	13.30
L1	.119	.135	3.03	3.43
L2	.098	.138	2.50	3.50
L3	.256	.295	6.50	7.50
L4	.906	.945	23.00	24.00
M	.177	.216	4.50	5.50
ØP	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

PRELIMINARY TECHNICAL INFORMATION

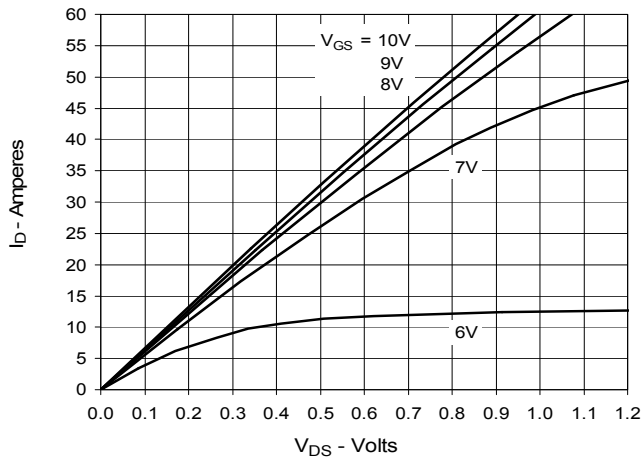
The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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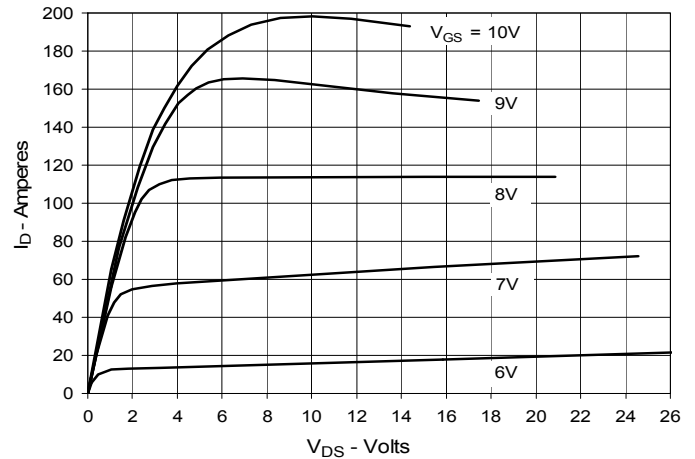
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

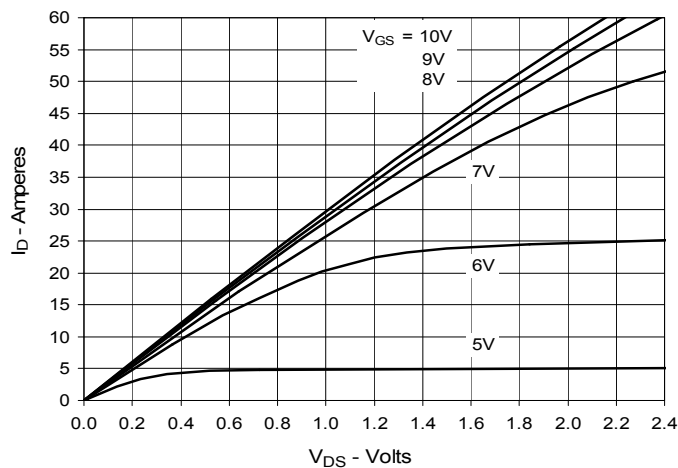
**Fig. 1. Output Characteristics
@ 25°C**



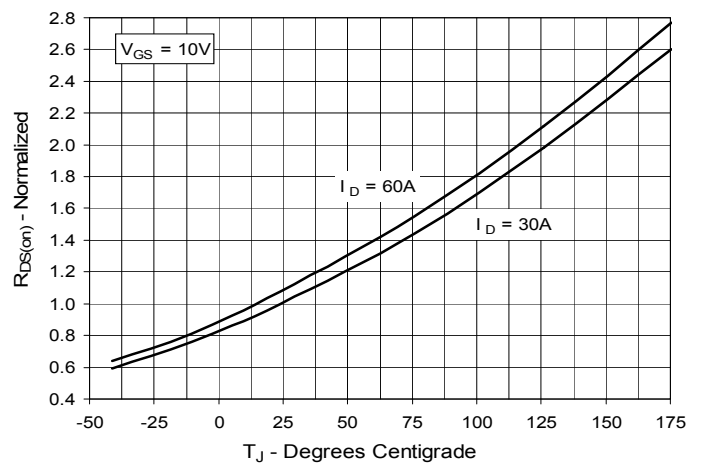
**Fig. 2. Extended Output Characteristics
@ 25°C**



**Fig. 3. Output Characteristics
@ 150°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 30A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 30A$ Value
vs. Drain Current**

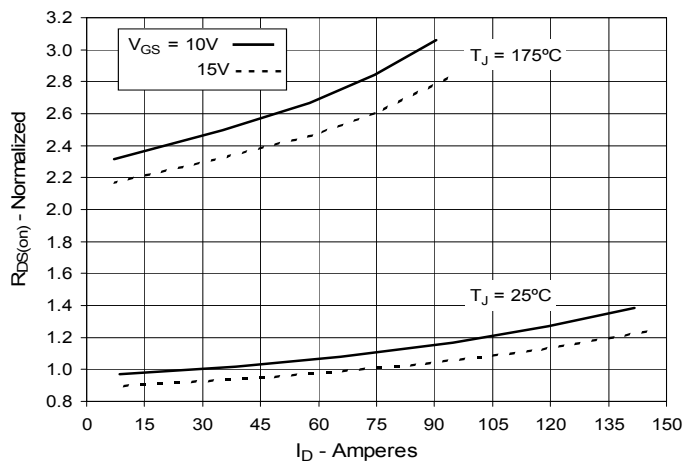


Fig. 6. Drain Current vs. Case Temperature

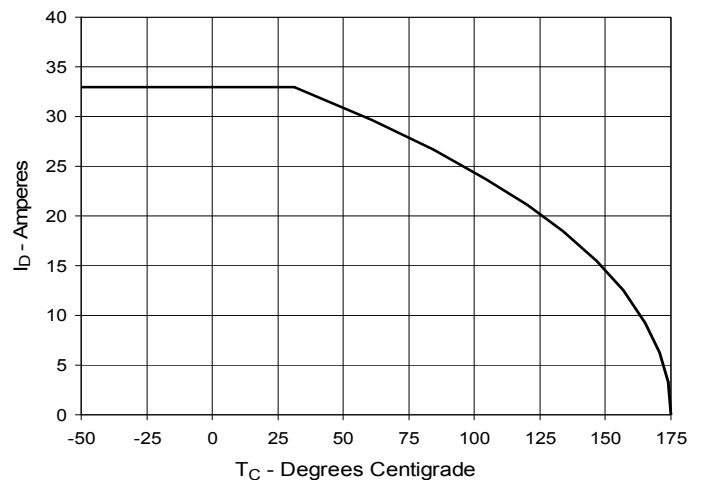


Fig. 7. Input Admittance

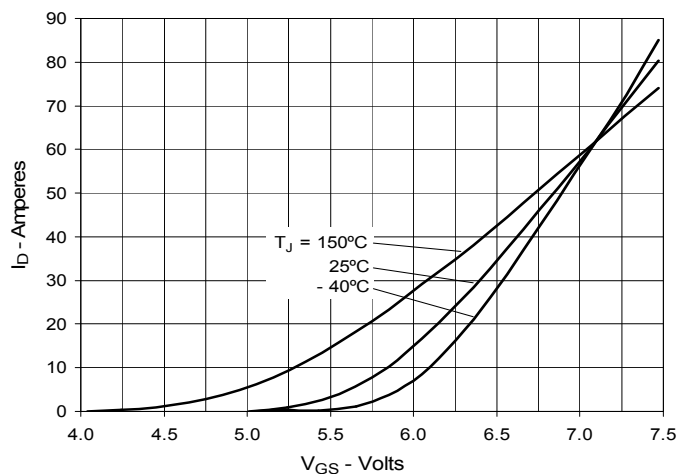


Fig. 8. Transconductance

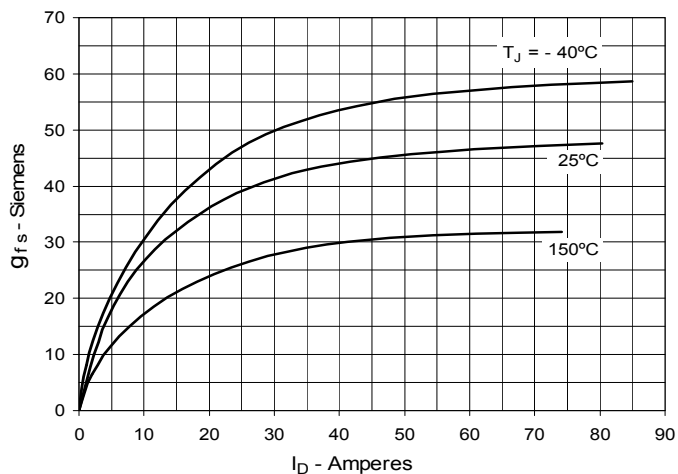


Fig. 9. Forward Voltage Drop of Intrinsic Diode

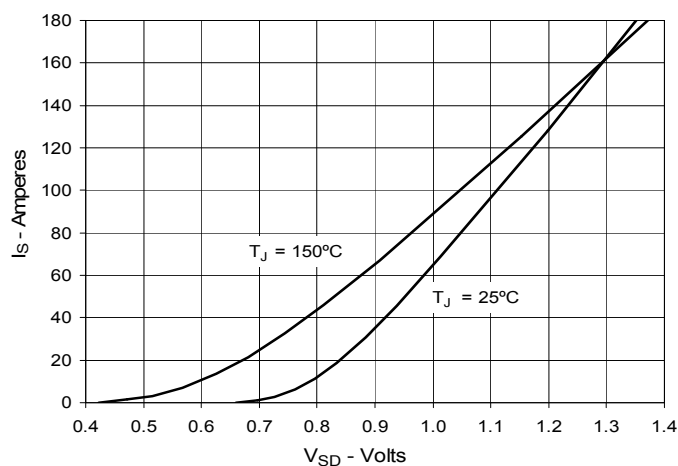


Fig. 10. Gate Charge

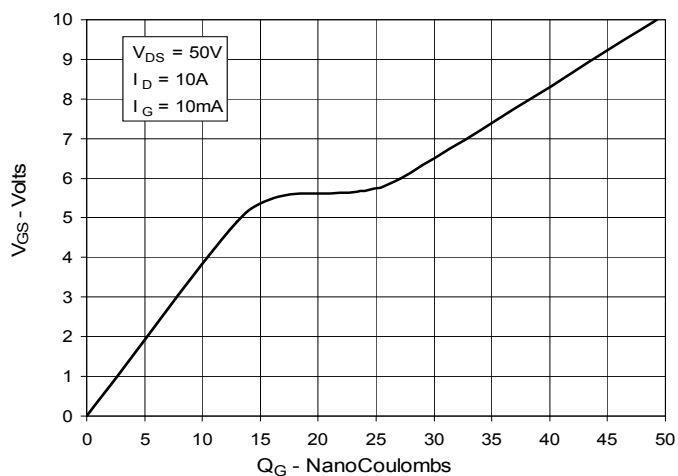


Fig. 11. Capacitance

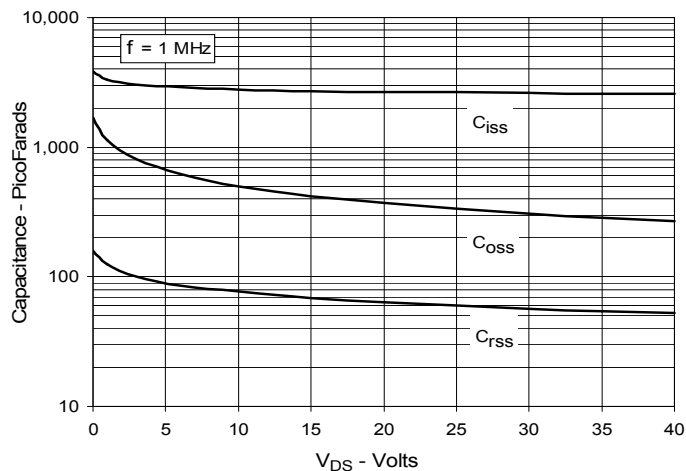
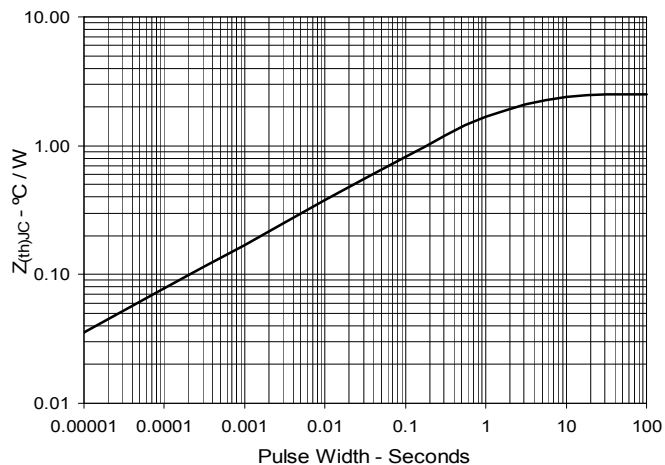
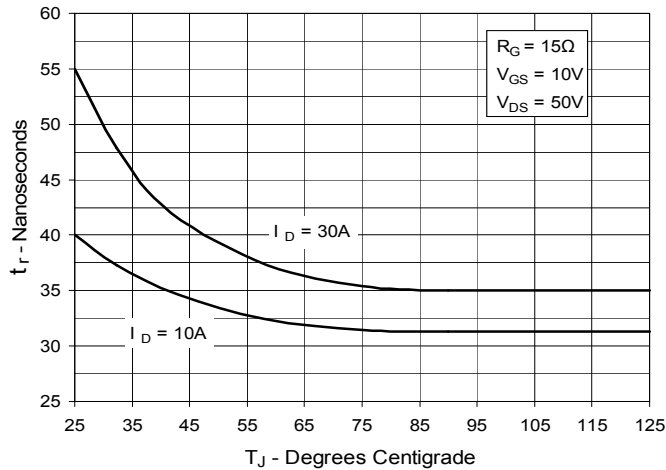
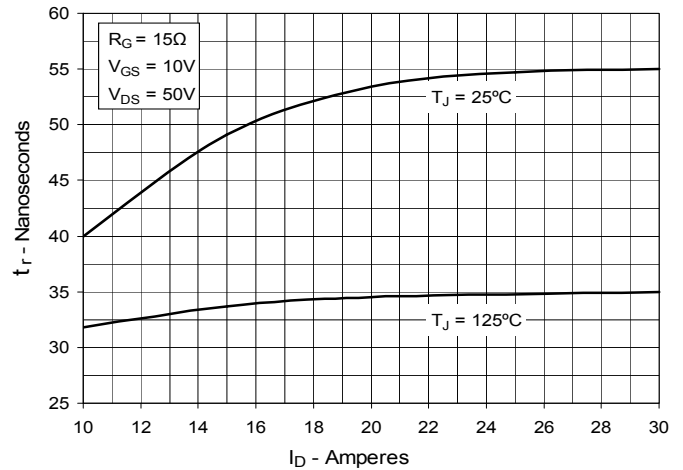
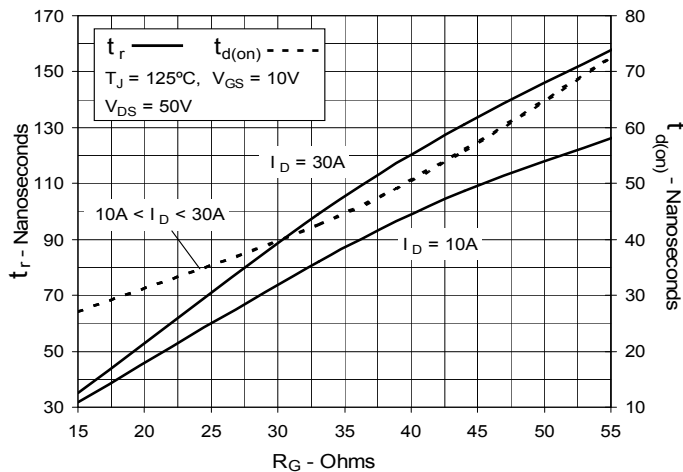
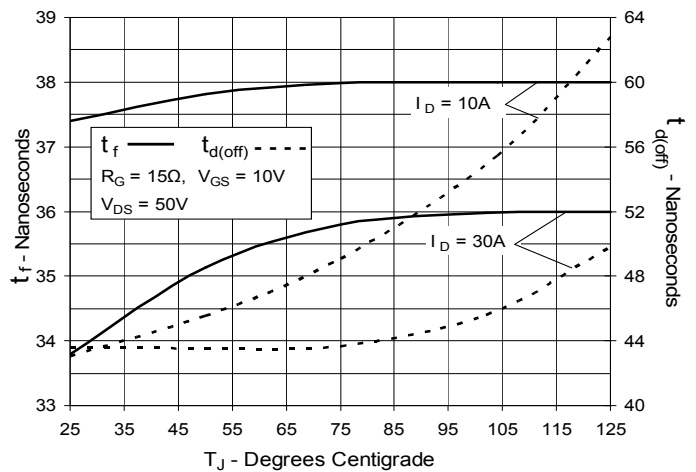
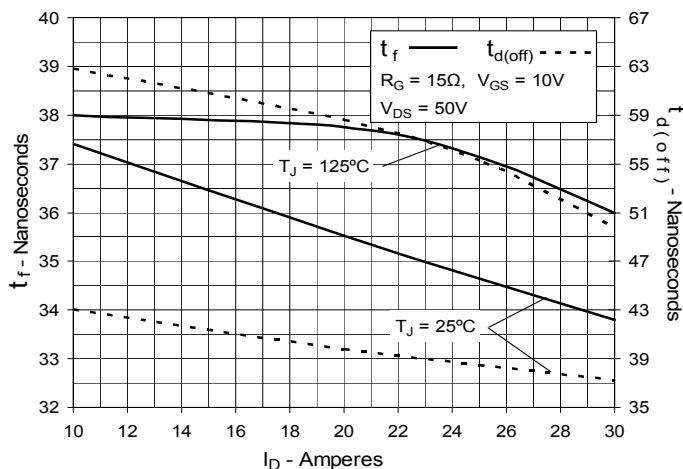


Fig. 12. Maximum Transient Thermal Impedance



IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance
